

Si-doped Zinc Oxide Transparent Conducting Oxides; Nanoparticle Optimisation, Scale-up and Thin Film Deposition

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Supplementary Information

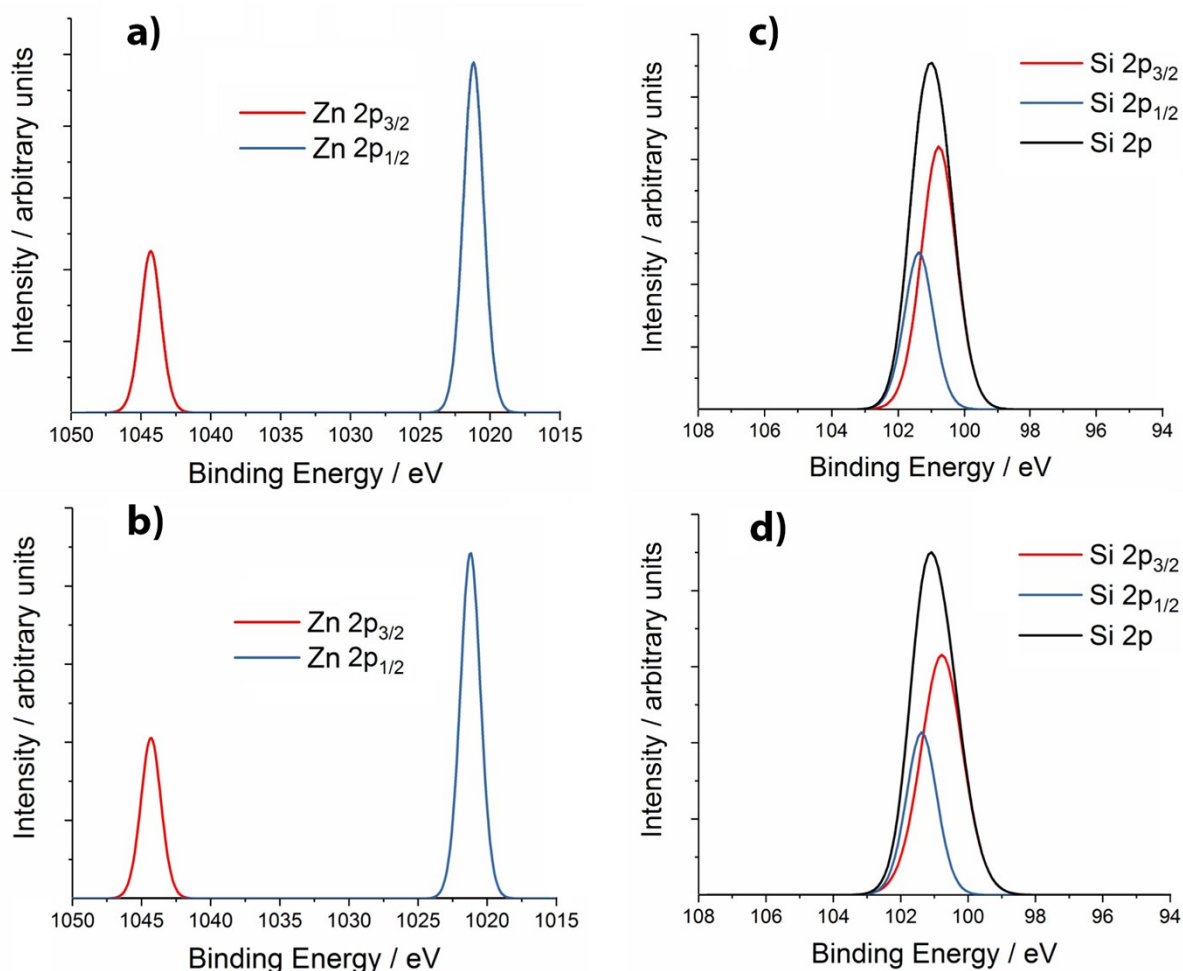


Figure S1. XPS spectra for a) and b) the Zn 2p binding energies for the 1.0 and 2.5 at% SiZO samples, respectively, and c) and d) the Si 2p binding energies for the 1.0 and 2.5 at% SiZO samples, respectively, as synthesised using the laboratory scale CHFS.

Table S1. Summarising the resistivity data across the compositional space explored. Data is for pressed, heat treated discs prepared from each of the powder samples.

Sample	Resistivity x 10 ⁻² / Ω cm
0.25 at% Si	3.50 ± 0.04
0.5 at% Si	5.93 ± 0.65
1.0 at% Si	8.87 ± 0.01
1.5 at% Si	11.84 ± 0.01
2.0 at% Si	15.95 ± 0.47
2.5 at% Si	30.57 ± 0.15
3.0 at% Si	119.73 ± 0.15
0.25 at% Si (pilot)	3.98 ± 0.10